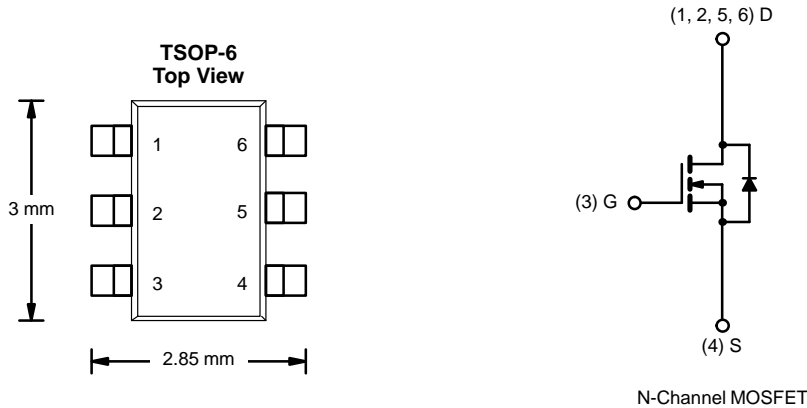




## N-Channel 200-V (D-S) MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
200	5 @ $V_{GS} = 10$ V	$\pm 0.42$



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter	Symbol	5 secs	Steady State	Unit
Drain-Source Voltage	$V_{DS}$	200		V
Gate-Source Voltage	$V_{GS}$	$\pm 20$		
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) <sup>a</sup>	$T_A = 25^\circ\text{C}$	$\pm 0.42$	$\pm 0.31$	A
	$T_A = 70^\circ\text{C}$	$\pm 0.34$	$\pm 0.25$	
Pulsed Drain Current (10 $\mu\text{s}$ Pulse Width)	$I_{DM}$	$\pm 0.75$		
Avalanche Current	$I_{AS}$	$\pm 0.75$		mJ
Single Avalanche Energy	$E_{AS}$	0.028		
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	$\pm 1$		A
Maximum Power Dissipation <sup>a</sup>	$T_A = 25^\circ\text{C}$	2.1	1.14	W
	$T_A = 70^\circ\text{C}$	1.34	0.73	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150		$^\circ\text{C}$

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 5$ sec	50	60	$^\circ\text{C/W}$
	Steady State	90	110	
Maximum Junction-to-Foot	Steady State	35	42	

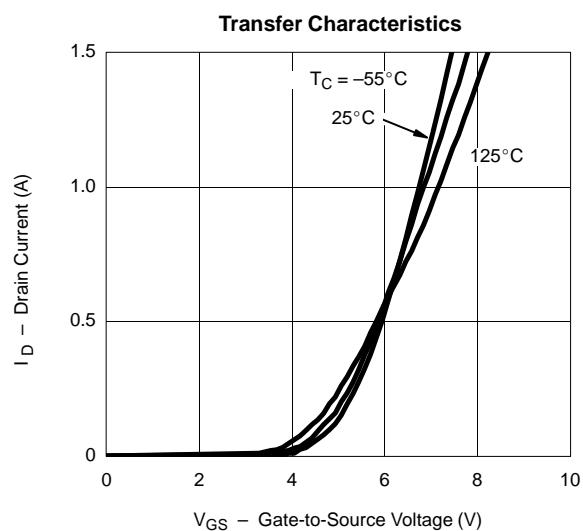
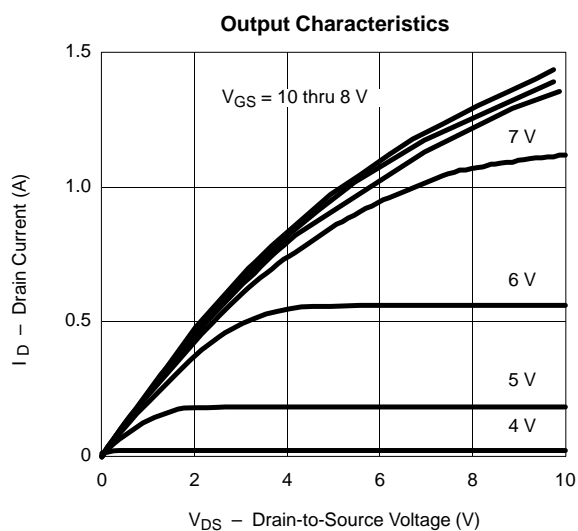
Notes  
a. Surface Mounted on 1" x 1" FR4 Board.


**SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2			V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 160 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 160 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			25	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	0.75			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.35 A			5	Ω
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 1 A		10		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = 1 A, V <sub>GS</sub> = 0 V			1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.5 A		2.1	3.4	nC
Gate-Source Charge	Q <sub>gs</sub>			0.5		
Gate-Drain Charge	Q <sub>gd</sub>			0.9		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 100 V, R <sub>L</sub> = 100 Ω I <sub>D</sub> ≅ 0.75 A, V <sub>GEN</sub> = 10 V, R <sub>G</sub> = 6 Ω		8	13	ns
Rise Time	t <sub>r</sub>			8	13	
Turn-Off Delay Time	t <sub>d(off)</sub>			9	15	
Fall Time	t <sub>f</sub>			30	50	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 1 A, di/dt = 100 A/μs		130	210	

## Notes

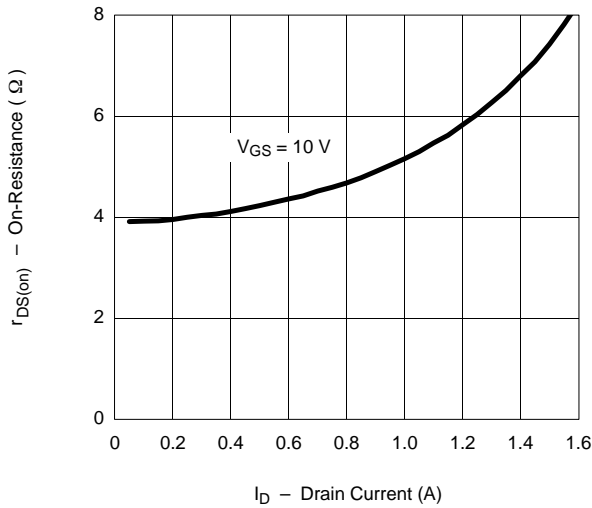
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.  
 b. Guaranteed by design, not subject to production testing.

**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**


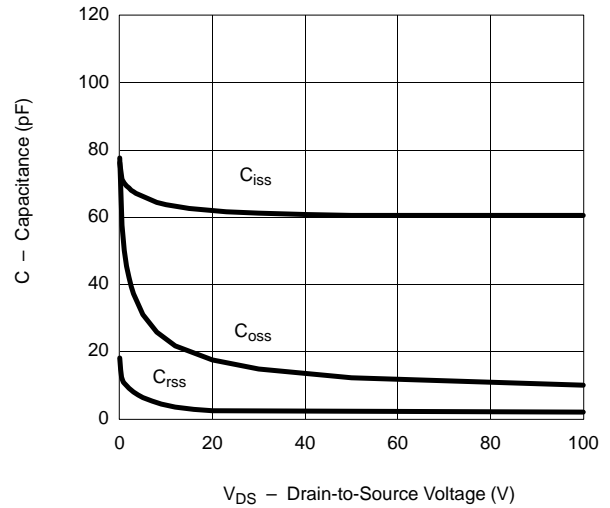


**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

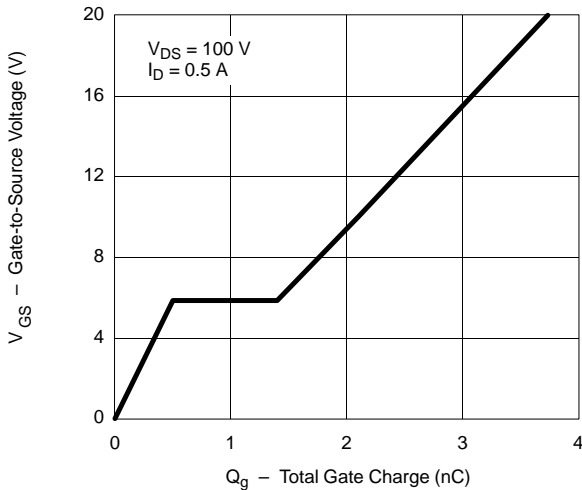
On-Resistance vs. Drain Current



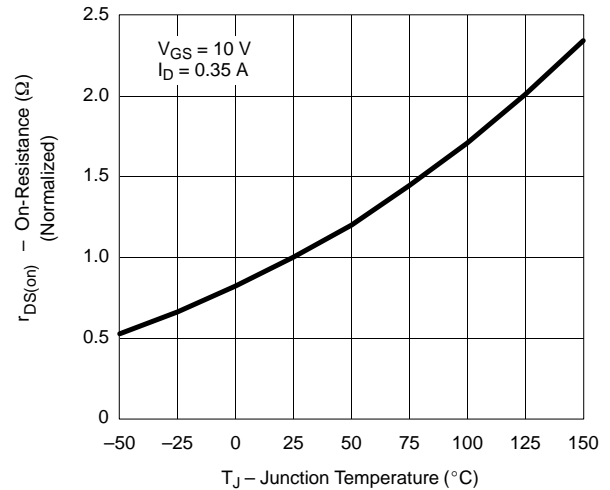
Capacitance



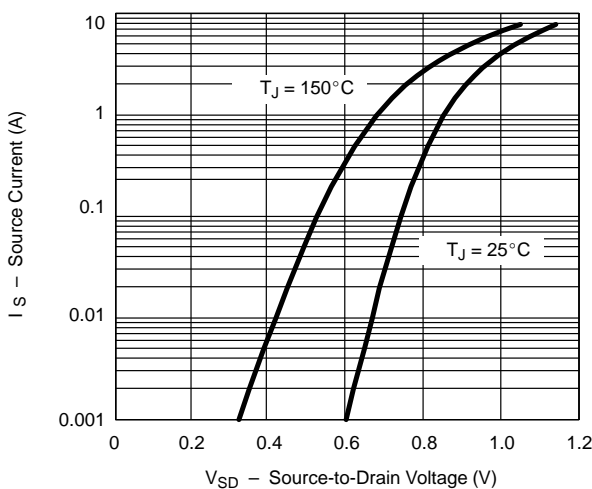
Gate Charge



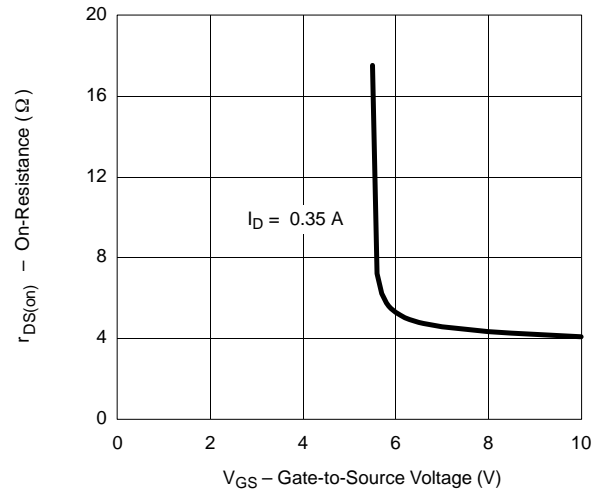
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage





**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

